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(71) Applicant (for all designated States except US):
NANYANG TECHNOLOGICAL UNIVERSITY
[SG/SG]; 50 Nanyang Avenue, Singapore 639798 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): POENAR, Daniel
Puiu [RO/SG]; 98 Nanyang Crescent #06-03, Singapore
637665 (SG). TSE, Man Siu [SG/SG]; 648D, Jurong West
Street 61., #15-222, Singapore 644648 (SG). CHEN, Jun
[CN/SG]; Block 912, Jurong West Street 91., #03-254, Sin-
gapore 640912 (SG).

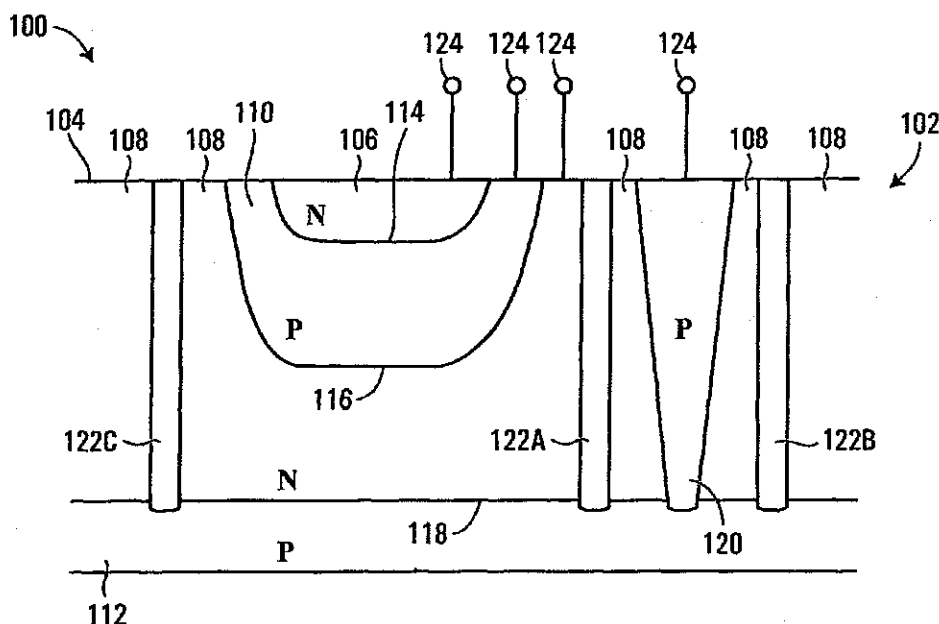
(74) Agent: ALBAN TAY MAHTANI & DE SILVA; 39
Robinson Road, #07-01 Robinson Point, Singapore
069811 (SG).

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(54) Title: METHOD AND DEVICE FOR WAVELENGTH-SENSITIVE PHOTO-SENSING USING MULTIPLE PN-JUNCTION



(57) Abstract: A photo-sensing cell (100) having vertically-stacked pn junctions (114, 116, 118) can include one or more insulation regions (122A, 122B, 122C) for laterally isolating adjacent regions in the cell and/or for laterally isolating the cell from an adjacent cell. The photo-sensing cell can be used alone or in an array of cells such as for forming light sensing pixels in a color sensing device. The sensing cell can be formed primarily by epitaxial growth to achieve good control of layer thickness, doping level and doping profile, and well-defined pn junctions.



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